

CLAIM AMENDMENTS

Please cancel Claims 1, 2, 4-24, and 26-38, and amend Claim 3 and 25 as follows:

1.-2. (Cancelled)

3. (Currently Amended) ~~The A~~ semiconductor member ~~according to claim 1, further comprising:~~

a first porous semiconductor layer which is made of a strain inducing material on a semiconductor substrate;

a strained semiconductor layer which is formed on the first porous semiconductor layer; and

a second porous semiconductor layer made of the same material as the semiconductor substrate between the semiconductor substrate and said first porous semiconductor layer made of the strain induction inducing material.

4.-24. (Cancelled)

25. (Currently Amended) ~~The A~~ semiconductor member ~~according to claim 20, further comprising:~~

a first porous semiconductor layer which is made of a strain inducing material on a semiconductor substrate;

a second porous semiconductor layer which is formed on the first porous semiconductor layer;

a strained semiconductor layer which is formed on the second porous semiconductor layer; and

a third porous semiconductor layer made of the same material as the semiconductor substrate between the semiconductor substrate and said first porous semiconductor layer made of the strain ~~induction~~inducing material.

26.-38. (Cancelled)